Ordering number:EN2983A

SB02W03C

Schottky Barrier Diode (Twin Type · Cathode Common)

30V, 200mA Rectifier

Applications

· High frequency rectification (switching regulators, converters, choppers).

Features

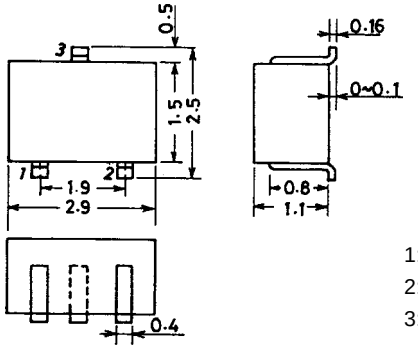
· Low forward voltage (V_F max=0.55V).
· Fast reverse recovery time (t_{rr} max=10ns).
· Low switching noise.
· Low leakage current and high reliability due to highly reliable planar structure.

Package Dimensions

unit:mm

1169A

[SB02W03C]



1:Anode
2:Anode
3:Cathode

SANYO:CP

Specifications

Absolute Maximum Ratings at Ta = 25˚C (Value per element)

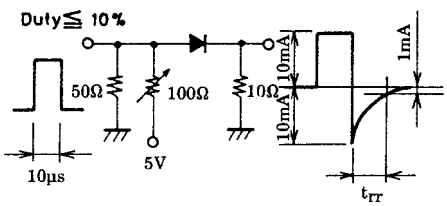
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		30	V
Non-repetitive Peak Reverse Surge Voltage	V_{RSM}		35	V
Average Output Current	I_O		200	mA
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	2	A
Junction Temperature	Tj		–55 to +125	˚C
Storage Temperature	Tstg		–55 to +125	˚C

Electrical Characteristics at Ta = 25˚C (Value per element)

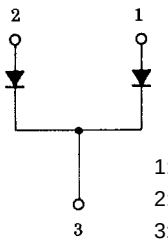
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=50μA	30			V
Forward Voltage	V_F	I_F=200mA			0.55	V
Reverse Current	I_R	V_R=15V			15	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		6.3		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=10mA, See specified Test Circuit			10	ns
Thermal Resistance (1)	Rth(j-a)1			525		˚C/W
Thermal Resistance (2)	Rth(j-a)2	Moutned on Cu-foild area of 16mm²×0.2mm on glass epoxy board		380		˚C/W

Marking : L

t_{rr} Test Circuit



Electrical Connection



1:Anode
2:Anode
3:Cathode

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